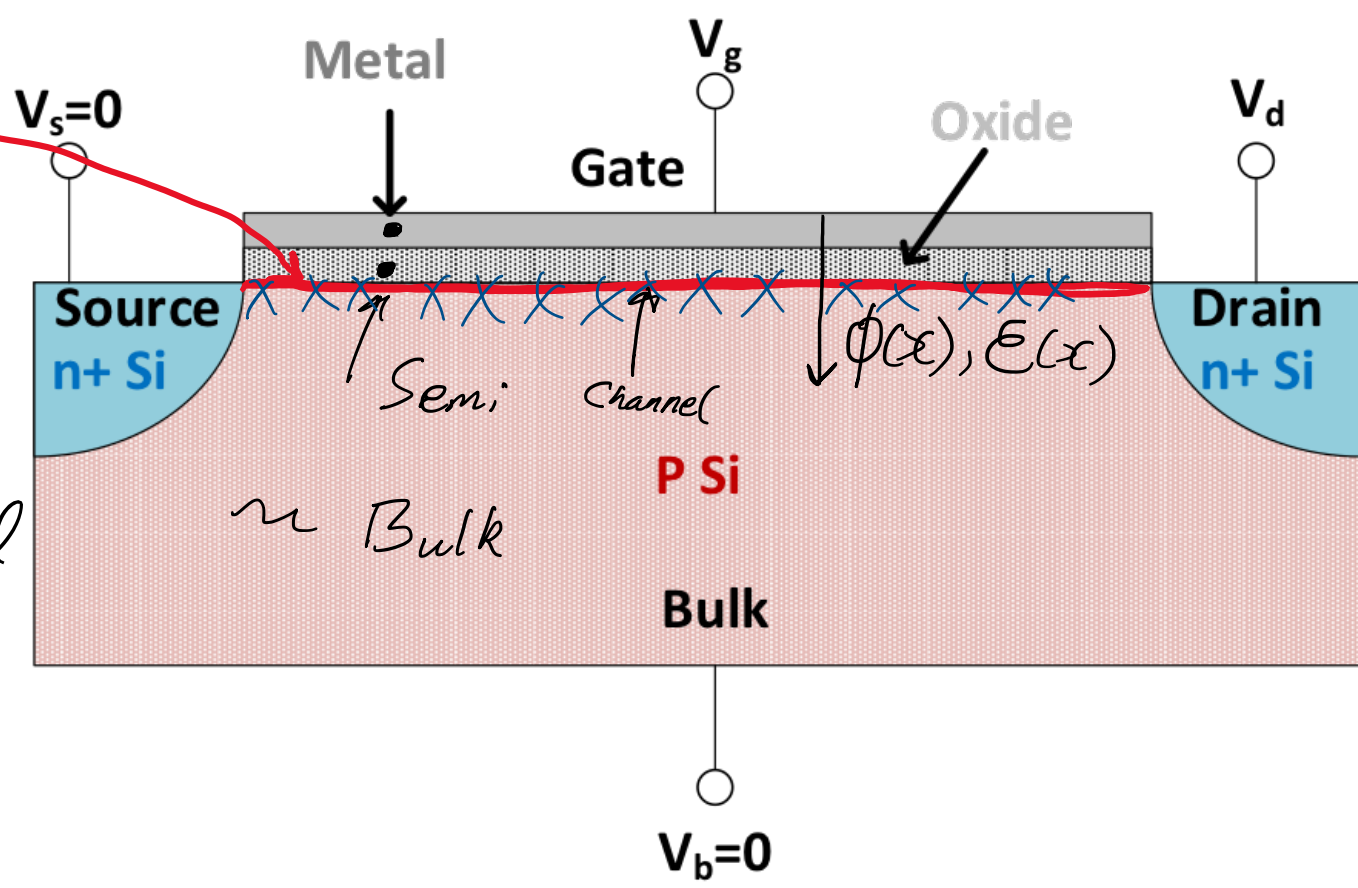


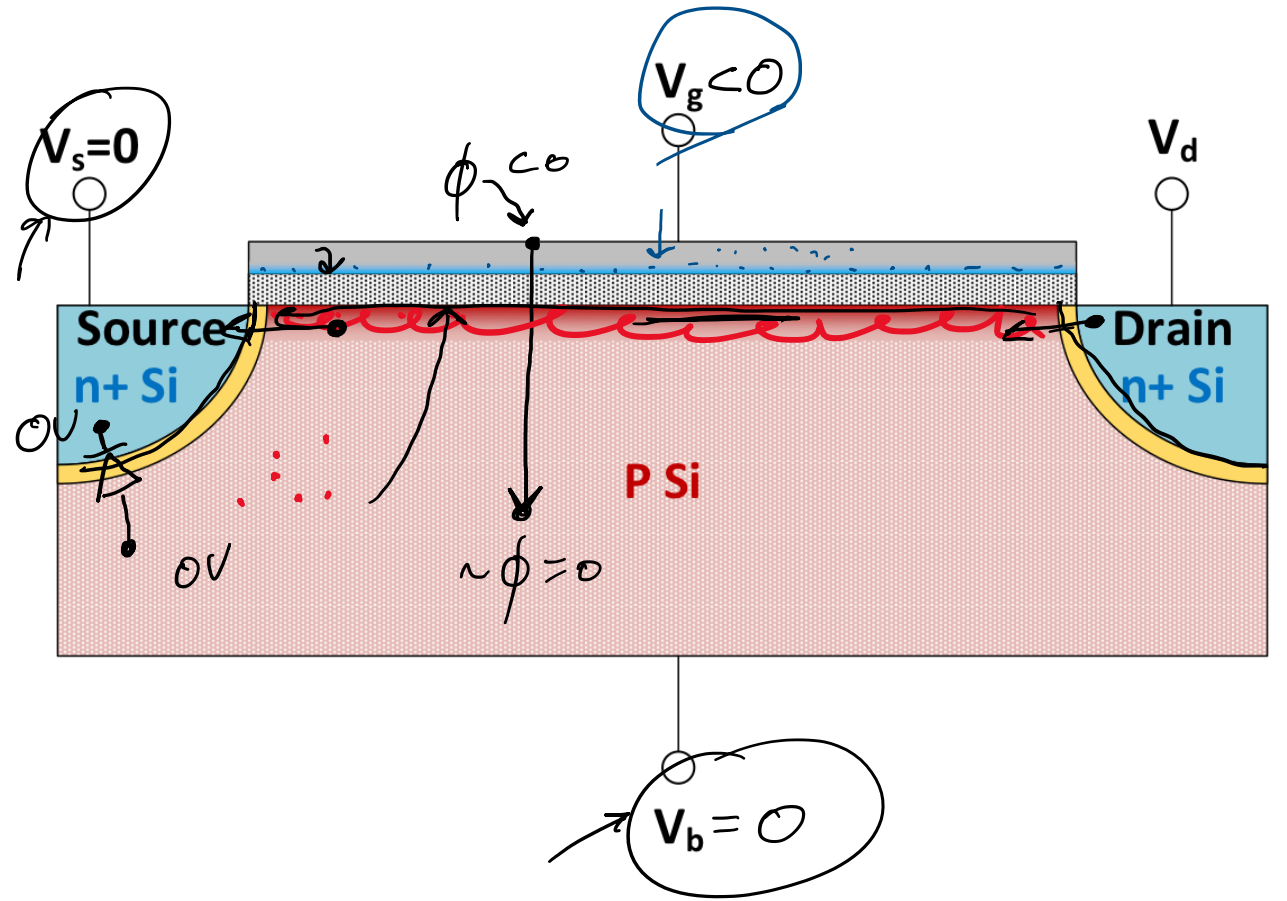
# What is MOS ?

- A transistor  
 ↳  $I$  in a channel is Modified by  $V_G$
- Metal → Oxide → Semi
- $V_G \rightarrow \phi(x) \rightarrow E(x) \rightarrow$  Move around Carriers



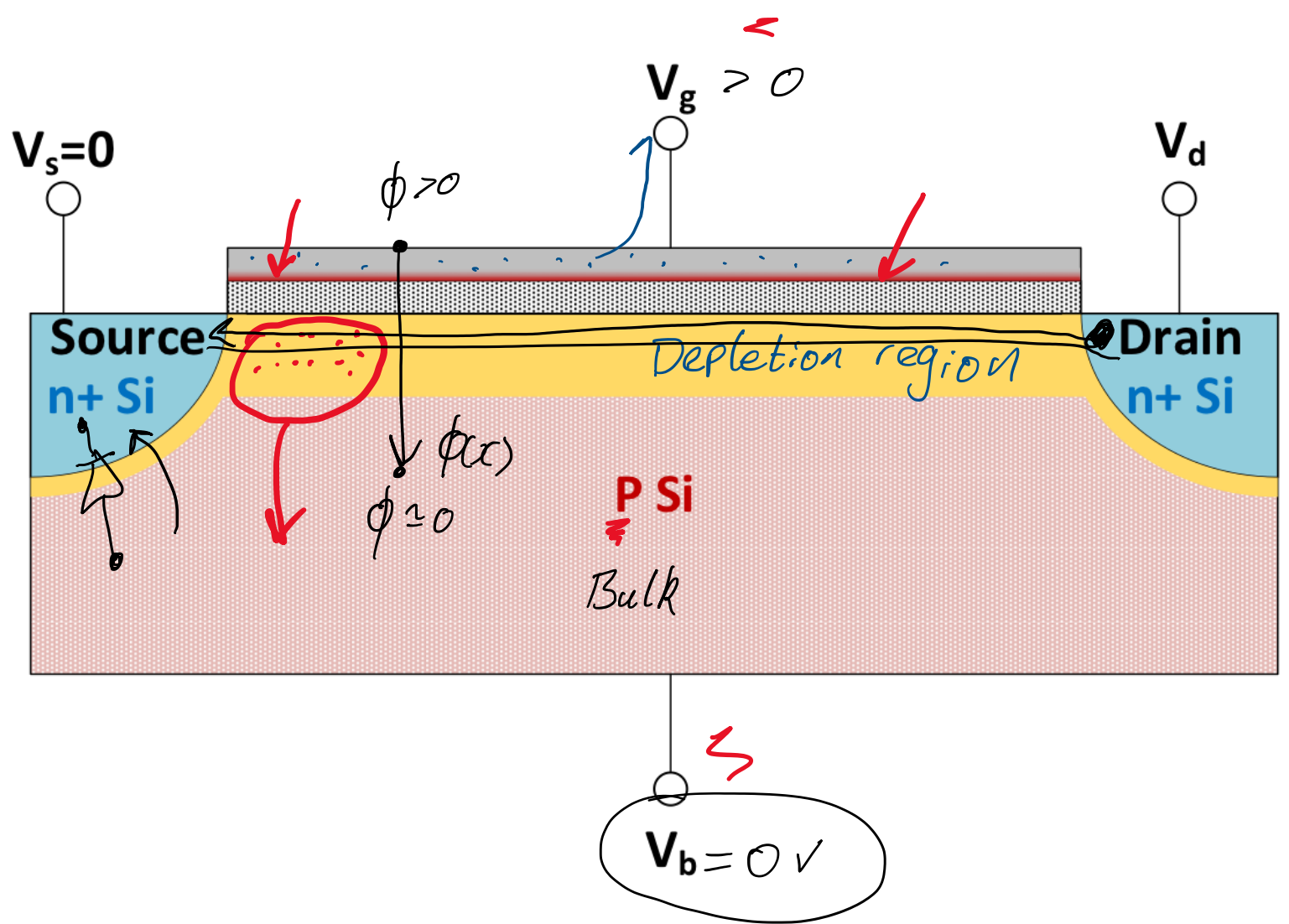
## Accumulation

- Set  $V_g = 0$
- Creates  $\phi$  gradient along device
- $e$  in gate → attracted to MO interface
- $h$  in the Bulk attracted to the SO interface
- No Conduction due to junction depletions → Device is off



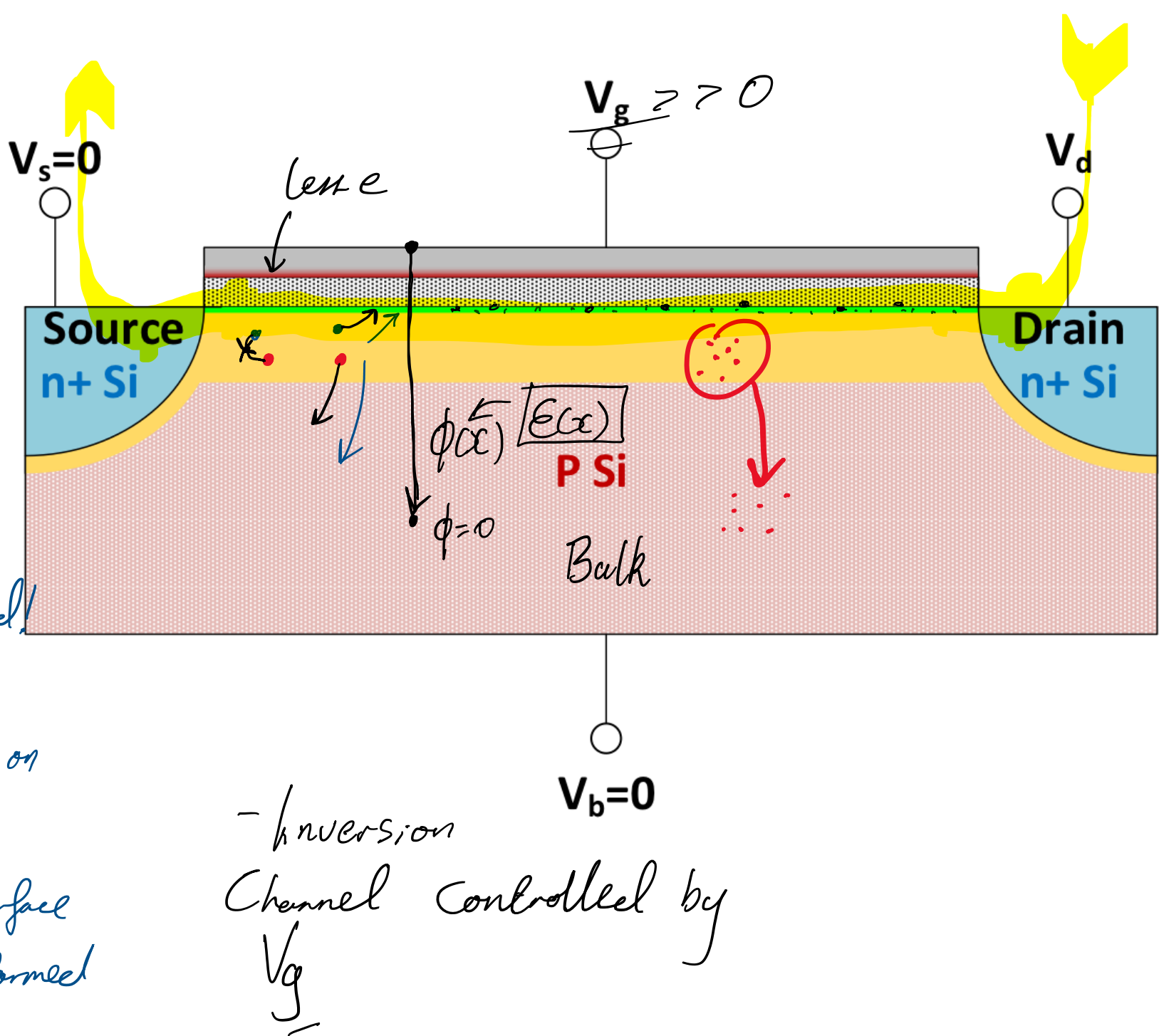
## Depletion

- $V_g > 0$ , Small  
 ↳ Positive  $\phi(x)$  near the channel
- holes pushed into Bulk
- ↳ Depletion region is formed in the channel
- No Conduction  
 ↳ Device is off



## Minority Carrier Inversion

- $V_g \gg 0$ , Large  
 ↳ large  $\phi(x)$   $G \rightarrow B$   
 "  $E(x)$
- less  $e$  MO interface
- $h$  are repelled from channel into bulk
- Looks like depletion!
- \*  $eh$  pairs always generated!
- In depletion, they recombine  
 ↳ not available for conduction
- $h$  is attracted to bulk
- $e$  is attracted to SO interface
- Conductive channel is formed
- The device is ON!! ✓



- Inversion Channel controlled by  $V_g$